

<Full SiC Power Modules>

FMF600DXZA-24B

 HIGH POWER SWITCHING USE
INSULATED TYPE


Dual switch (Half-Bridge)

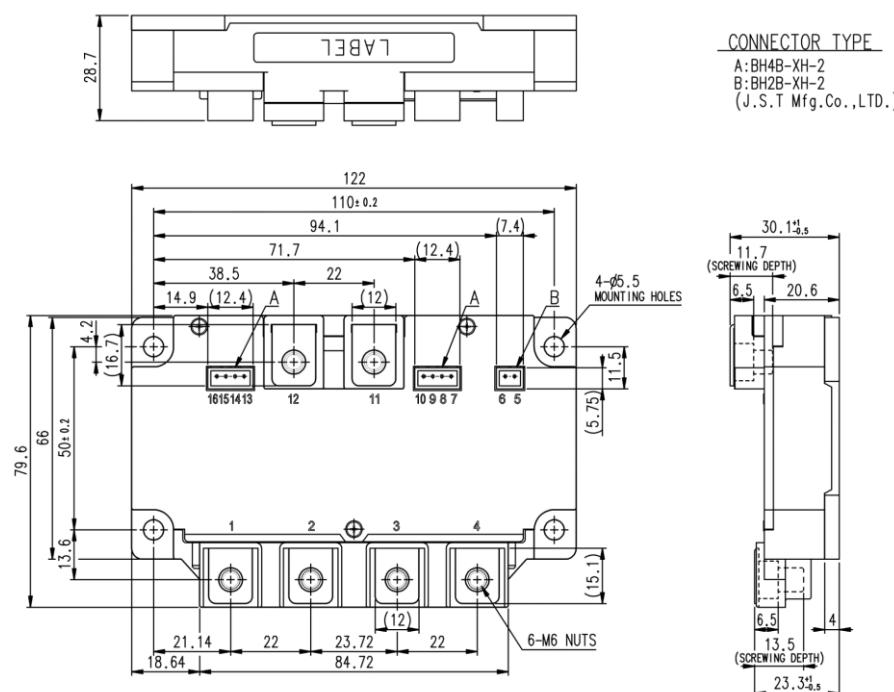
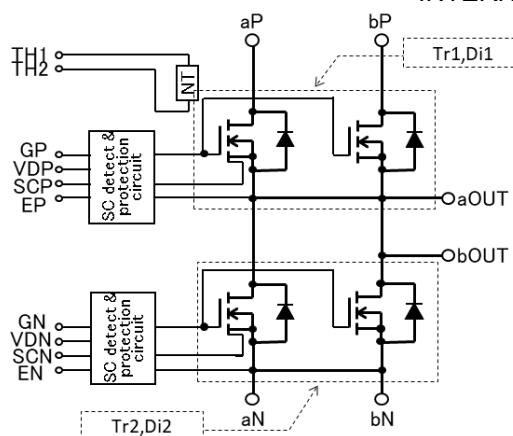
Drain current I_D 600 A
 Drain-Source voltage V_{DSX} 1200 V
 Maximum junction temperature T_{vjmax} 175 °C
 •Silicon Carbide MOSFET + Silicon Carbide Schottky Barrier Diode
 •Flat base Type
 •Copper base plate
 •RoHS Directive compliant
 •Recognized under UL1557, File E323585

APPLICATION

AC Motor Control, Motion/Servo Control, Power supply, etc.

OUTLINE DRAWING & INTERNAL CONNECTION

Dimension in mm


INTERNAL CONNECTION


Terminal	code
1	aP
2	aN
3	bN
4	bP
5	TH1
6	TH2
7	VDN
8	SCN
9	GN
10	EN
11	bOUT
12	aOUT
13	EP
14	GP
15	SCP
16	VDP

Tolerance otherwise specified		
Division of Dimension	Tolerance	
0.5	to 3	±0.2
over 3	to 6	±0.3
over 6	to 30	±0.5
over 30	to 120	±0.8
over 120	to 400	±1.2

 aP and bP, aN and bN, aOUT-bOUT
must be connected externally.

FMF600DXZA-24BHIGH POWER SWITCHING USE
INSULATED TYPE**MAXIMUM RATINGS (T_{vj} = 25 °C, unless otherwise specified)**

Symbol	Item	Conditions	Rating	Unit
V _{DSX}	Drain-source voltage	V _{GS} =-15 V	1200	V
V _{GSS}	Gate-source voltage	D-S short-circuited	±20	V
I _D	Drain current	DC, T _C =55°C (Note.2)	600	A
I _{DRM}	I _D	Pulse, Repetitive (Note.3), T _{vj} =150°C (Note.4)	900	
P _{tot}	Total power dissipation	T _C =25 °C (Note.2)	2230	W
I _S (Note.1)	Source current	DC	600	A
I _{SRM} (Note.1)	I _S	Pulse, Repetitive (Note.3), T _{vj} =150°C	900	
V _{isol}	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	5000	V
T _{vjmax}	Maximum junction temperature	Instantaneous event (overload) (Note.10)	175	°C
T _{vjop}	Operating junction temperature	Continuous operation (under switching) (Note.10)	-40~+150	°C
T _{cmax}	Maximum case temperature	(Note.2, 10)	125	°C
T _{stg}	Storage temperature	-	-40~+125	°C

ELECTRICAL CHARACTERISTICS (T_{vj}=25 °C, unless otherwise specified)

Symbol	Item	Conditions (note9)		Limits		Unit	
			Min.	Typ.	Max.		
I _{DSX}	Drain-source cut-off current	V _{DS} =V _{DSX} , V _{GS} =-15 V	-	-	5.4	mA	
		V _{DS} =800V, V _{GS} =-15 V	-	-	0.54		
V _{GSS(th)}	Gate-source threshold voltage	I _D =171 mA, V _{DS} =10 V	1.8	2.2	2.6	V	
I _{GSS}	Gate-source leakage current	V _{GS} =V _{GSS} , D-S short-circuited	-	-	0.5	µA	
V _{DS(on)} (terminal)	Drain-source on-state voltage	I _D =600 A, V _{GS} =15V (Note.6)	T _{vj} =25 °C	-	1.65	2.30	
			T _{vj} =125 °C	-	2.10	-	
			T _{vj} =150 °C	-	2.20	-	
V _{DS(on)} (chip)	Drain-source on-state voltage	I _D =600 A, V _{GS} =15V (Note.6)	T _{vj} =25 °C	-	1.35	-	
			T _{vj} =125 °C	-	1.80	-	
			T _{vj} =150 °C	-	1.90	-	
r _{DS(on)} (chip)	Drain-source on-state resistance	I _D =600 A, V _{GS} =15V (Note.6)	T _{vj} =25 °C	-	2.3	-	
			T _{vj} =125 °C	-	3.0	-	
			T _{vj} =150 °C	-	3.2	-	
C _{iss}	Input capacitance	V _{DS} =10 V, V _{GS} =0V	-	51	-	nF	
C _{oss}	Output capacitance		-	36	-		
C _{rss}	Reverse transfer capacitance		-	2.6	-		
Q _G	Gate charge	V _{DD} =600 V, I _D =600 A, V _{GS} =0→15 V	-	1463	-	nC	
t _{d(on)}	Turn-on delay time	V _{DD} =600 V, I _D =600 A, V _{GS} =±15 V, T _{vj} =150°C, R _G =0.5Ω, L _{s_ext} =12nH, Inductive load, per pulse	-	118	-	ns	
t _r	Rise time		-	46	-		
t _{d(off)}	Turn-off delay time		-	174	-		
t _f	Fall time		-	28	-		
E _{on}	Turn-on switching energy		-	8.82	-		
E _{off}	Turn-off switching energy		-	8.93	-		
Q _C	Drain-source charge	I _S =600 A (Note.6) V _{GS} =-15 V	-	2.9	-	µC	
V _{SD} (Note.1) (terminal)	Source-drain voltage		T _{vj} =25 °C	-	2.04	2.6	
			T _{vj} =125 °C	-	2.82	-	
			T _{vj} =150 °C	-	3.10	-	
V _{SD} (Note.1) (chip)	Source-drain voltage	I _S =600 A (Note.6) V _{GS} =-15 V	T _{vj} =25 °C	-	1.74	-	
			T _{vj} =125 °C	-	2.52	-	
			T _{vj} =150 °C	-	2.80	-	

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal resistance ^(Note. 2)	Junction to case, per inverter switch	-	-	67	K/kW
$R_{th(j-c)D}$		Junction to case, per inverter FWD	-	-	87	
$R_{th(c-s)}$	Contact thermal resistance ^(Note.2)	Case to heat sink, per 1 module, Thermal grease applied ^(Note.8, 10)	-	12	-	K/kW

NTC THERMISTOR PART

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R_{25}	Zero-power resistance	$T_c=25\text{ }^{\circ}\text{C}$ ^(Note.2)	4.85	5.00	5.15	k Ω
$\Delta R/R$	Deviation of resistance	$T_c=100\text{ }^{\circ}\text{C}$ ^(Note.2) , $R_{100}=493\text{ }\Omega$	-7.3	-	+7.8	%
$B_{(25/50)}$	B-constant	Approximate by equation ^(Note.7)	-	3375	-	K
P_{25}	Power dissipation	$T_c=25\text{ }^{\circ}\text{C}$ ^(Note.2)	-	-	10	mW

MODULE

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M_t	Mounting torque	Main terminals	M 6 screw	3.5	4.0	4.5
M_s		Mounting to heat sink	M 5 screw	2.5	3.0	6.0
e_c	Flatness of base plate	On the centerline X, Y ^(Note.5)	-100	-	+100	μm
-	Connector insertion force	2 pin type	0	-	25	N
		4 pin type	0	-	35	N

Symbol	Item	Conditions	Value	Unit
m	Mass	-	500	g
d_a	Clearance	Terminal to terminal	10	mm
d_s	Creepage distance	Terminal to terminal	17	mm
$R_{DD'+SS'}$	Internal lead resistance	P-EP, OUT-EN terminals, Per switch	0.5	m Ω
L_s	Internal stray inductance	P-N	10	nH
$r_{g(on)}$	Internal gate resistance (on)	Per switch	1.55	Ω
$r_{g(off)}$	Internal gate resistance (off)	Per switch	1.55	Ω

*: This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU and (EU)2015/863.

Note1. Represent ratings and characteristics of the anti-parallel, source-drain free wheeling diode (FWD).

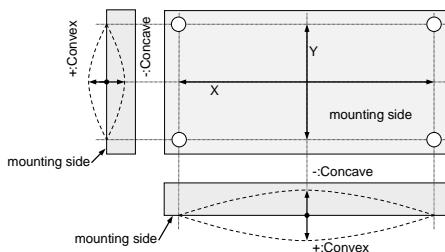
2. Case temperature (T_c) and heat sink temperature (T_s) are defined on the each surface (mounting side) of base plate and heat sink just under the chips.

Refer to the figure of chip location.

3. Pulse width and repetition rate should be such that the device junction temperature (T_{vj}) does not exceed $T_{vj\max}$ rating.

4. Junction temperature (T_{vj}) should not increase beyond $T_{vj\max}$ rating.

5. The base plate (mounting side) flatness measurement points (X, Y) are as follows of the following figure.



6. Pulse width and repetition rate should be such as to cause negligible temperature rise.

$$7. B_{(25/50)} = \ln\left(\frac{R_{25}}{R_{50}}\right) / \left(\frac{1}{T_{25}} - \frac{1}{T_{50}}\right)$$

R_{25} : resistance at absolute temperature T_{25} [K]; $T_{25}=25\text{ }^{\circ}\text{C}+273.15=298.15\text{ [K]}$

R_{50} : resistance at absolute temperature T_{50} [K]; $T_{50}=50\text{ }^{\circ}\text{C}+273.15=323.15\text{ [K]}$

8. Reference value. Thermally conductive grease of $\lambda=0.9\text{ W/(m}\cdot\text{K)}$ / $D_{(c-s)}=100\mu\text{m}$.

9. Per switch (ex. Tr1 chips total in page.6)

10. Long term performance related to thermal conductive grease (including but not limited to aspects such as the increase of thermal resistance due to pumping out, etc.) should be verified under your specific application conditions. Each temperature condition ($T_{vj\max}$, $T_{vj\text{ op}}$, $T_c\max$) must be maintained below the maximum rated temperature throughout consideration of the temperature rise even for long term usage.

FMF600DXZA-24BHIGH POWER SWITCHING USE
INSULATED TYPE**RECOMMENDED OPERATING CONDITIONS**

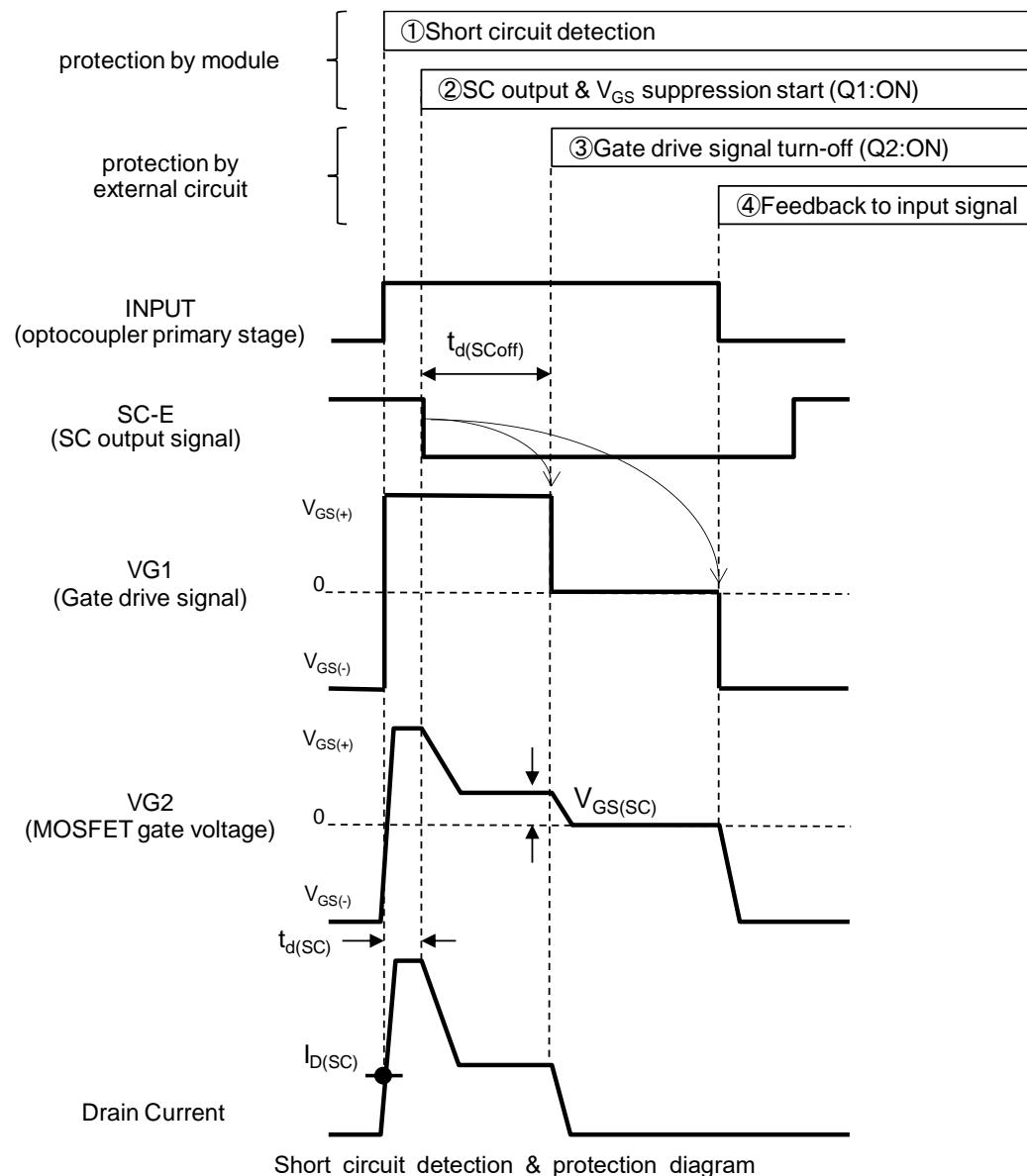
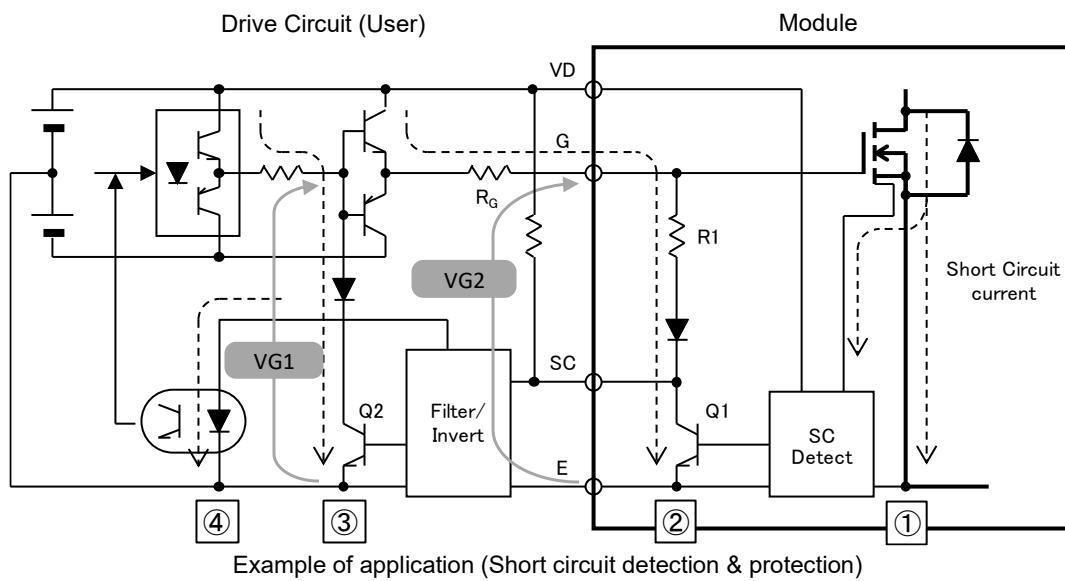
Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
V_{DD}	(DC) Supply voltage	Applied across aP -aN, bP-bN terminals	-	600	850	V	
V_D	DC supply voltage (control)	Applied across VDP-EP, VDN-EN terminals	13.5	15.0	16.5	V	
$V_{GS(+)}$	Gate-Source positive drive voltage	Applied across GP-EP, GN-EN terminals	13.5	15.0	16.5	V	
$V_{GS(-)}$	Gate-Source negative drive voltage	Applied across GP-EP, GN-EN terminals	-16.5	-15.0	-7.0	V	
R_G	External gate resistance ^(Note.11)	Per switch	On	0.5	-	1.5	Ω
			Off	0.5	-	10.0	Ω
f_C	Switching frequency	$V_{GS}=\pm 15V$, $R_G=0.5\Omega$, $V_{DD}=600V$, $T_{vj}=150^\circ C$	-	-	50	KHz	
$t_{d(SCoff)}$	Gate cutoff delay time after SC output	$V_{GS}=15V$, $R_G=0.5\Omega$, $V_{DD}\leq 850V$, $T_{vj}=150^\circ C$	-	-	3	μs	

Note 11. The value of external gate resistance should be considered the surge voltage not to exceed the rating voltage in the worst system condition.

SHORT CIRCUIT DETECTION & PROTECTION CHARACTERISTICS

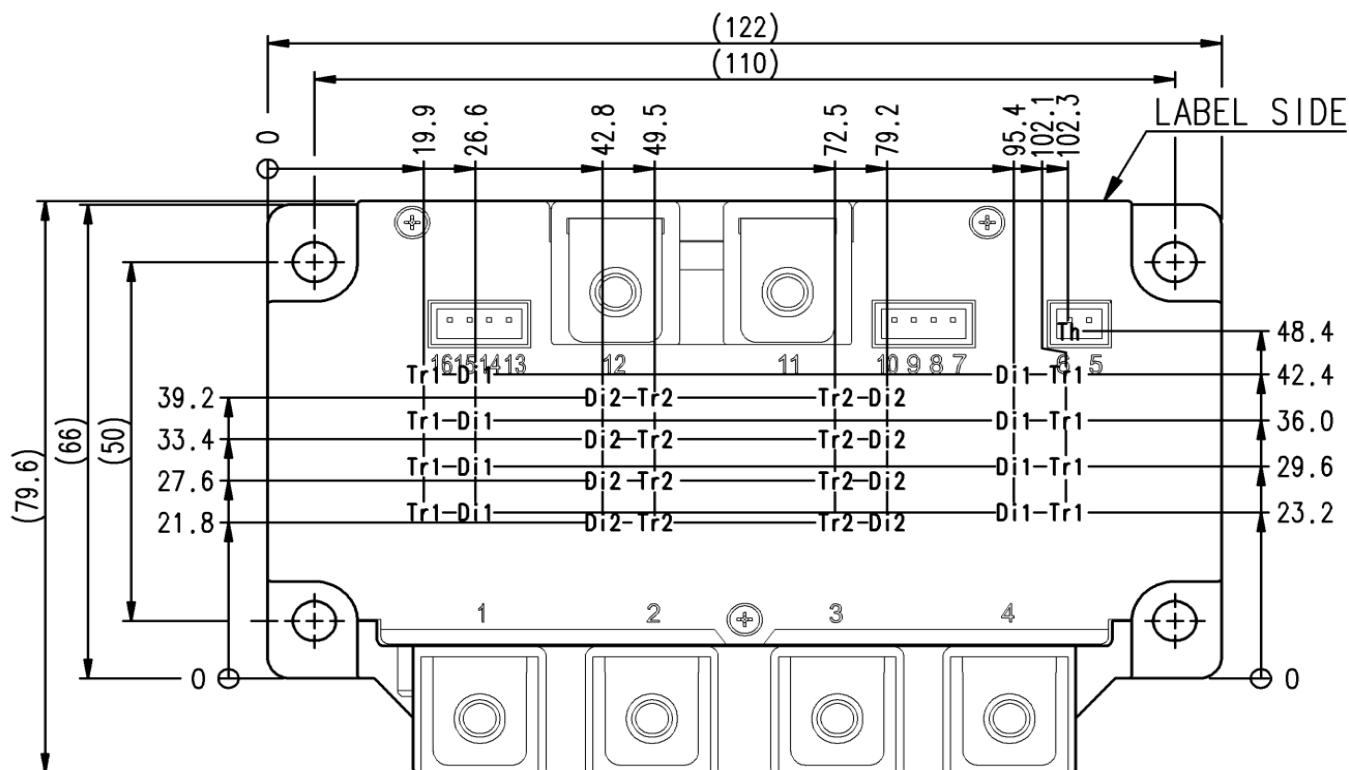
Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$I_{D(SC)}$	SC detect drain current	$T_{vj}=150^\circ C$, $V_{GS}=15V$	900	1200	-	A
$t_{d(SC)}$	SC detect delay time	$T_{vj}=150^\circ C$, $V_{GS}=15V$, $R_G=0.5\Omega$	-	1	-	μs
$V_{GS(SC)}$	SC protection gate limit voltage	$T_{vj}=150^\circ C$, $V_{GS}=15V$, $R_G=0.5\Omega$	-	6.0	-	V
R1	SC protection gate limit resistance	-	-	0.33	-	Ω

Refer to the circuit in page.5

SHORT CIRCUIT DETECTION & PROTECTION

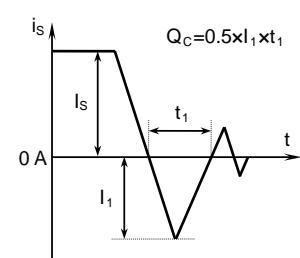
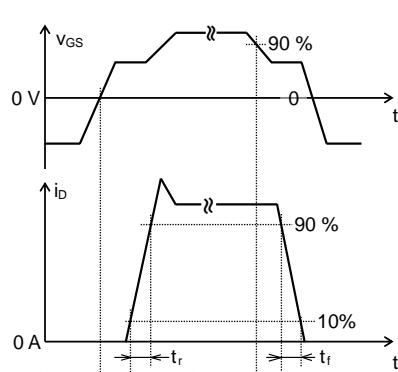
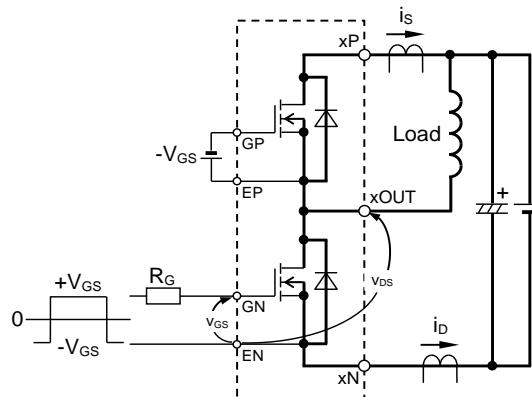
CHIP LOCATION (Top view)

Dimension in mm, tolerance: ± 1 mm



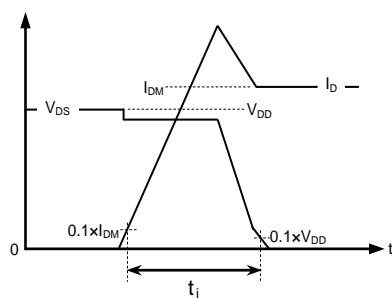
Tr1,Tr2: SiC-MOSFET, Di1,Di2: SiC-SBD, Th: NTC thermistor

TEST CIRCUIT AND WAVEFORMS

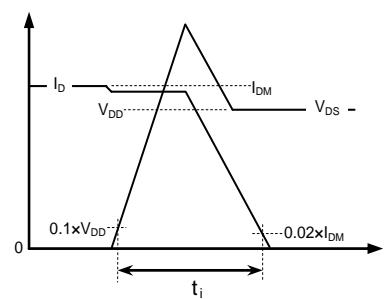


Switching characteristics test circuit and waveforms(x: connected a* and b*)

QC test waveform



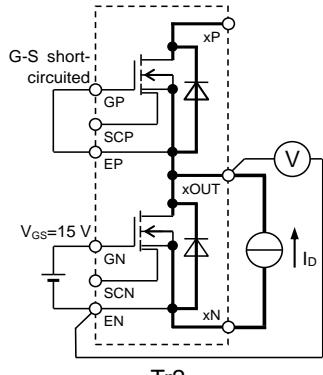
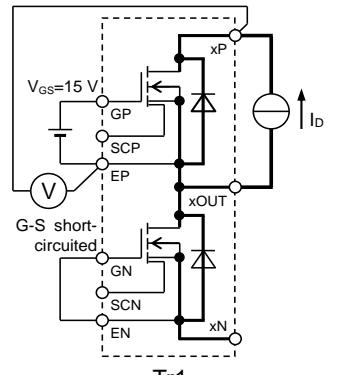
MOSFET Turn-on switching energy



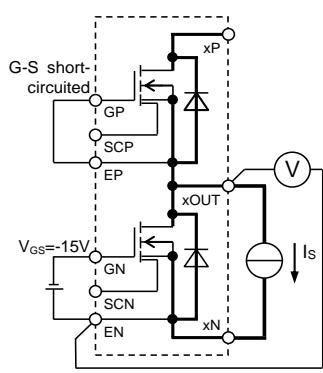
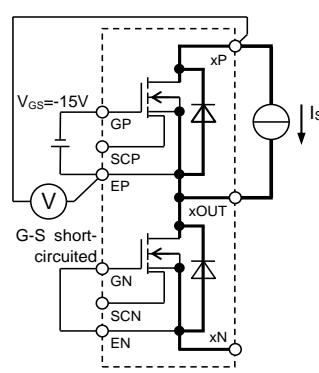
MOSFET Turn-off switching energy

Turn-on / Turn-off switching energy test waveforms (Integral time instruction drawing)

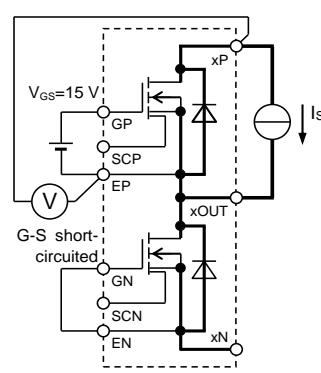
TEST CIRCUIT



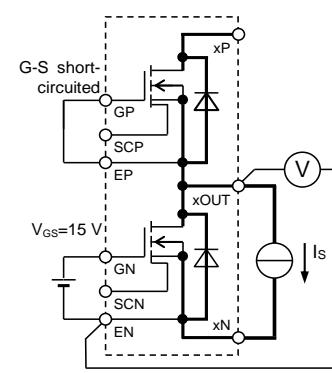
V_{DS}(on) test circuit (x: Connected a* and b*)



V_{SD} test circuit, V_{GS} = -15V (x: Connected a* and b*)



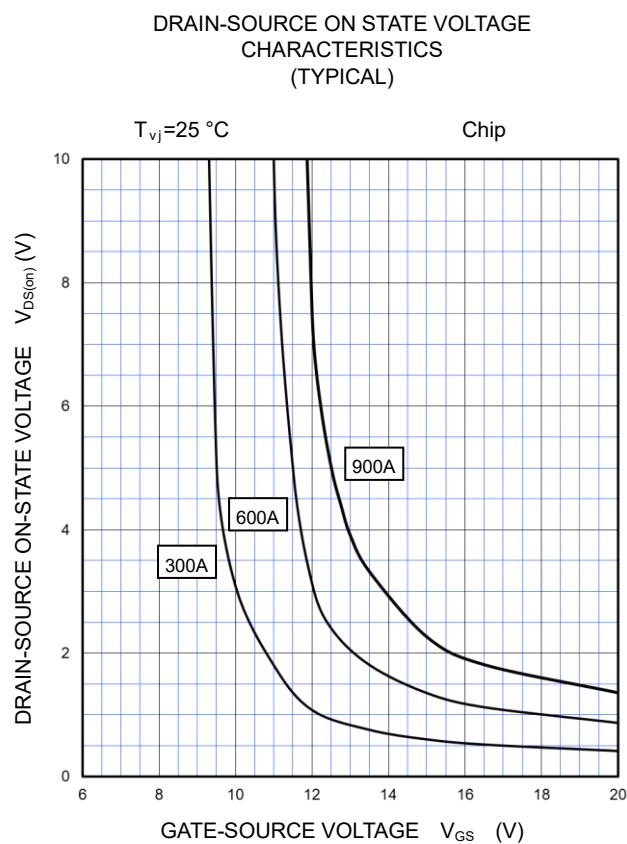
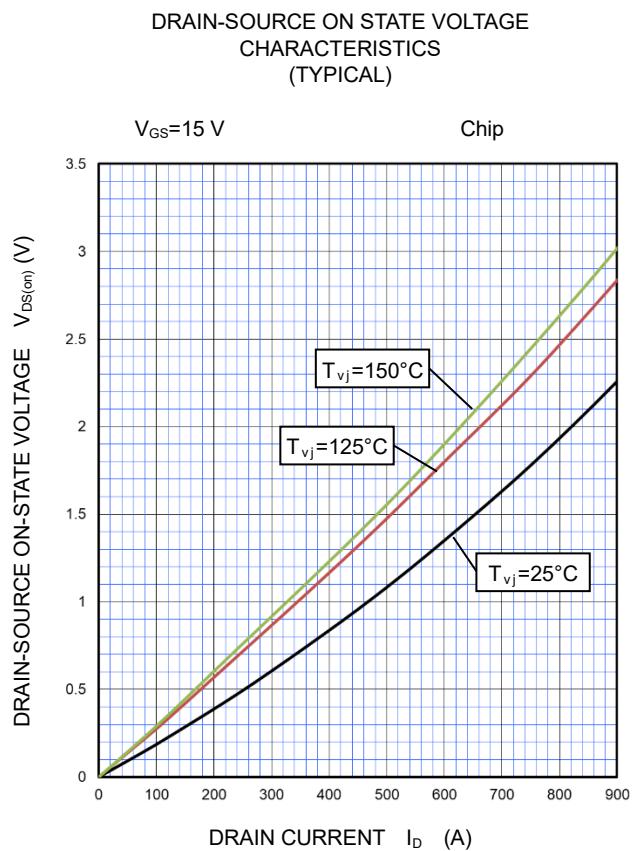
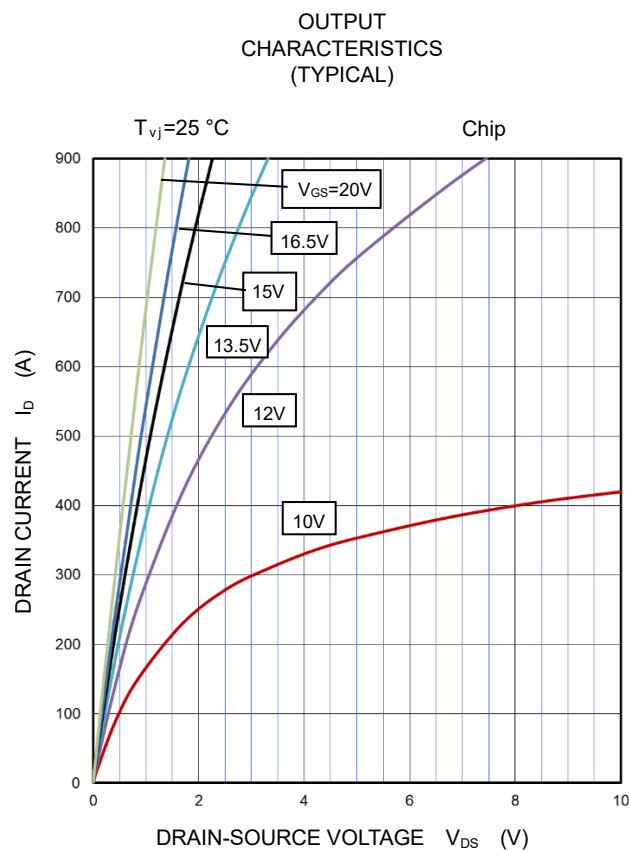
Tr1&Di1

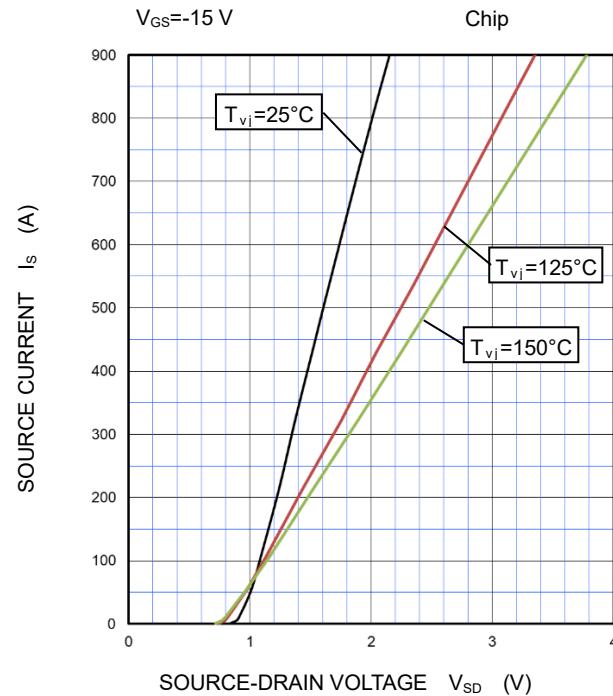
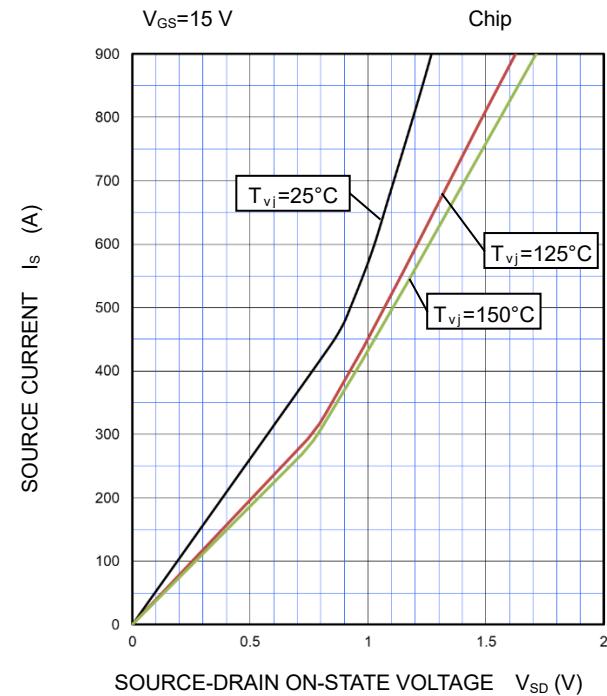
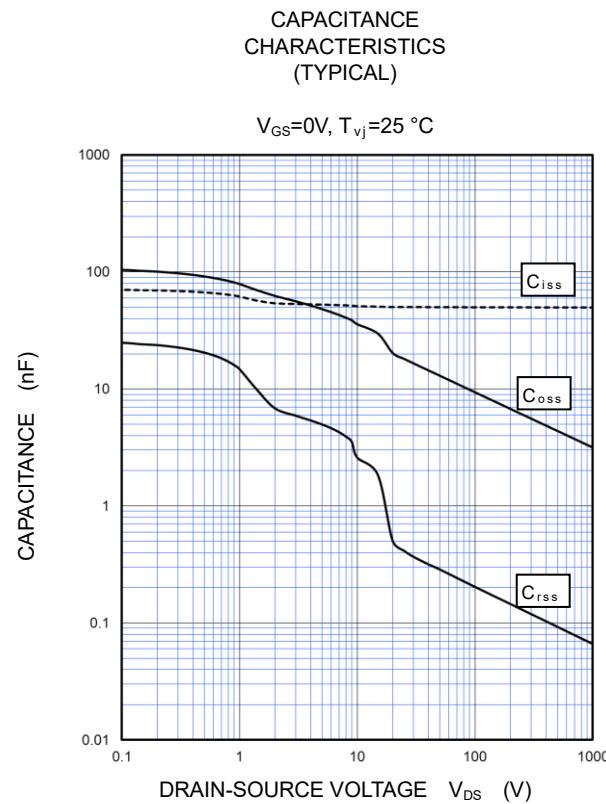
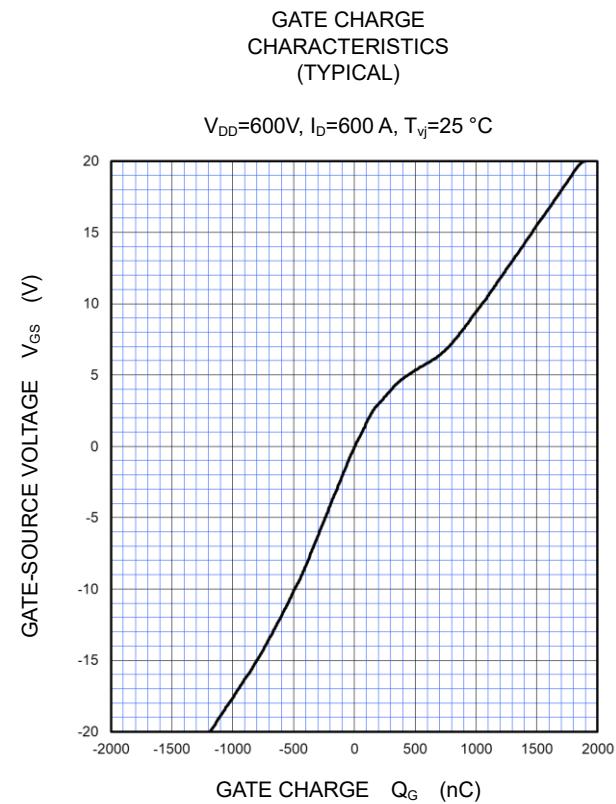


Tr2&Di2

V_{SD} test circuit, V_{GS} = 15V (x: Connected a* and b*)

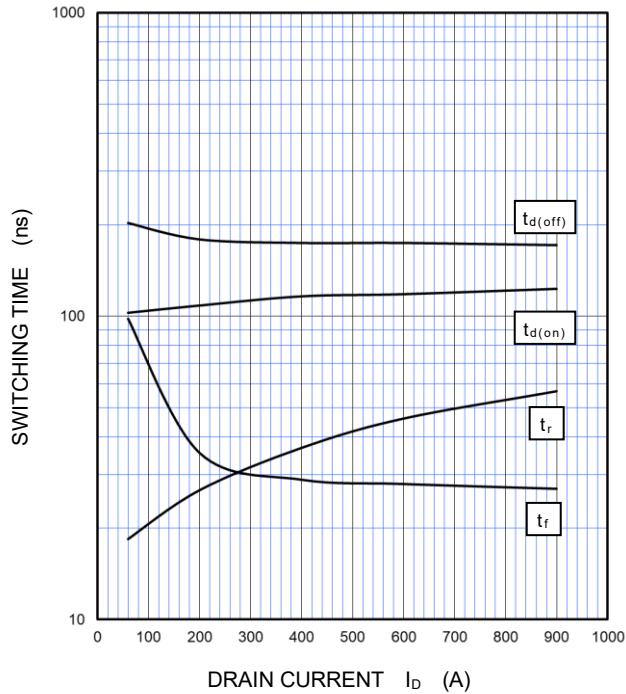
PERFORMANCE CURVES



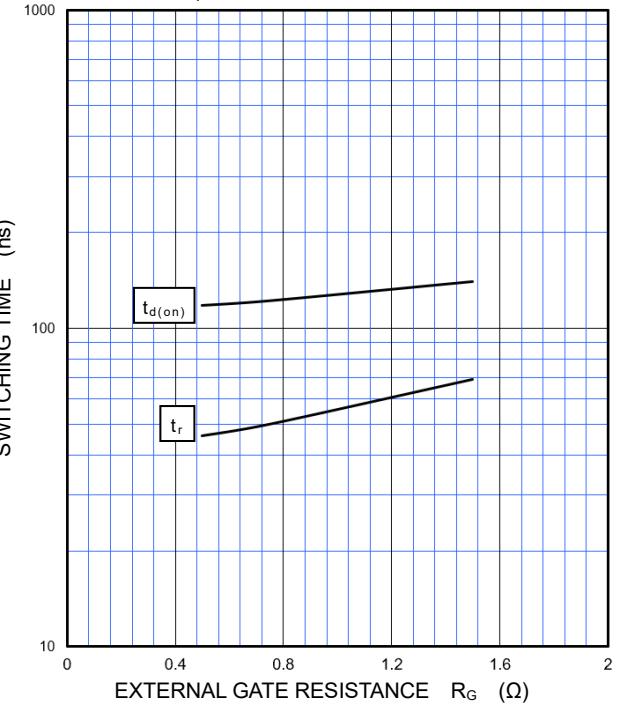
PERFORMANCE CURVESFREE WHEELING DIODE
FORWARD CHARACTERISTICS
(TYPICAL)SOURCE-DRAIN ON STATE VOLTAGE
CHARACTERISTICS
(TYPICAL)CAPACITANCE
CHARACTERISTICS
(TYPICAL)GATE CHARGE
CHARACTERISTICS
(TYPICAL)

PERFORMANCE CURVES**HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)**

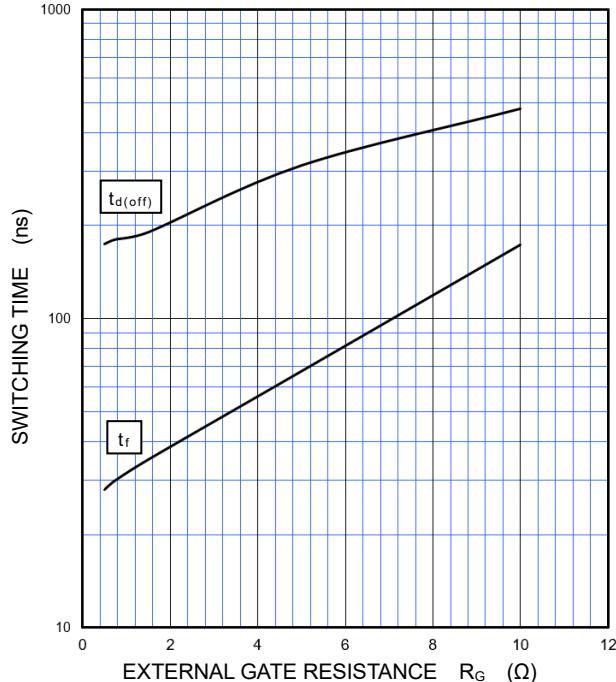
$V_{DD}=600$ V, $V_{GS}=\pm 15$ V, $R_G=0.5$ Ω , $L_{s_ext}=12$ nH
 $T_{vj}=150$ $^{\circ}$ C, INDUCTIVE LOAD

**HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)**

$V_{DD}=600$ V, $V_{GS}=\pm 15$ V, $I_D=600$ A, $L_{s_ext}=12$ nH
 $T_{vj}=150$ $^{\circ}$ C, INDUCTIVE LOAD

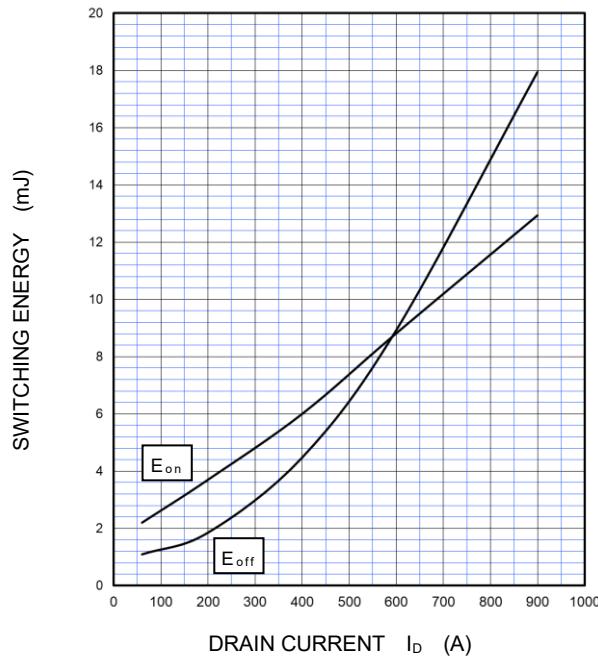
**HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)**

$V_{DD}=600$ V, $V_{GS}=\pm 15$ V, $I_D=600$ A, $L_{s_ext}=12$ nH
 $T_{vj}=150$ $^{\circ}$ C, INDUCTIVE LOAD

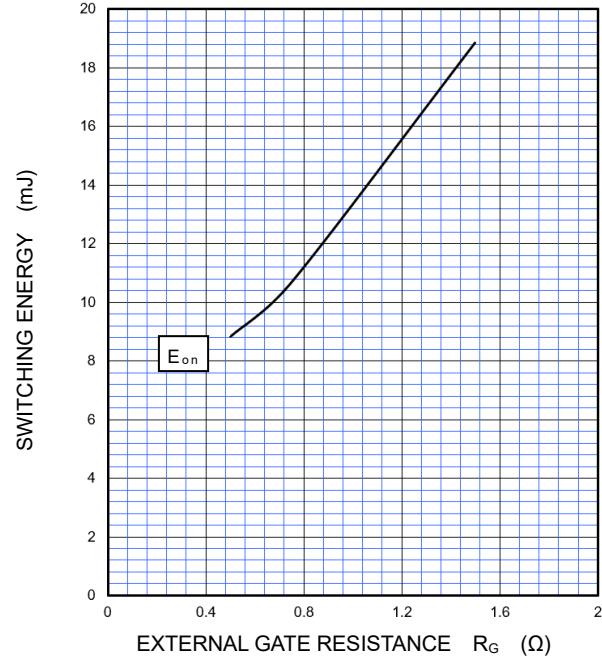


PERFORMANCE CURVESHALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

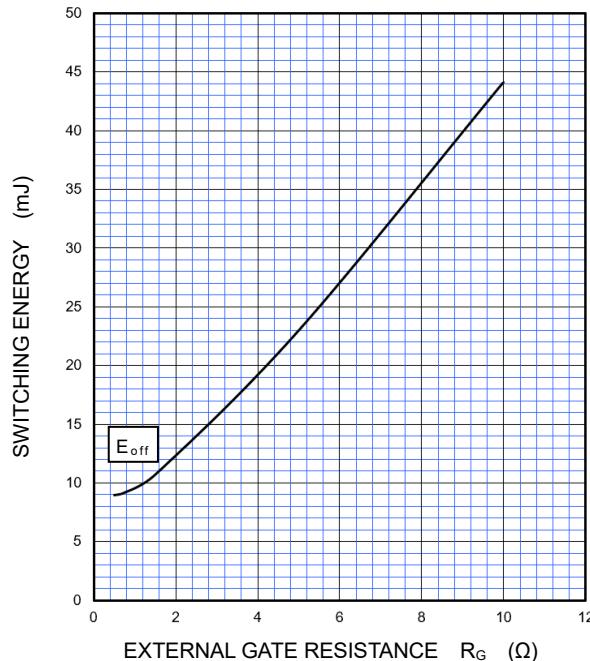
$V_{DD}=600\text{ V}$, $V_{GS}=\pm 15\text{ V}$, $R_G=0.5\Omega$, $T_{vj}=150\text{ }^\circ\text{C}$, $L_{s_ext}=12\text{nH}$
INDUCTIVE LOAD, PER PULSE

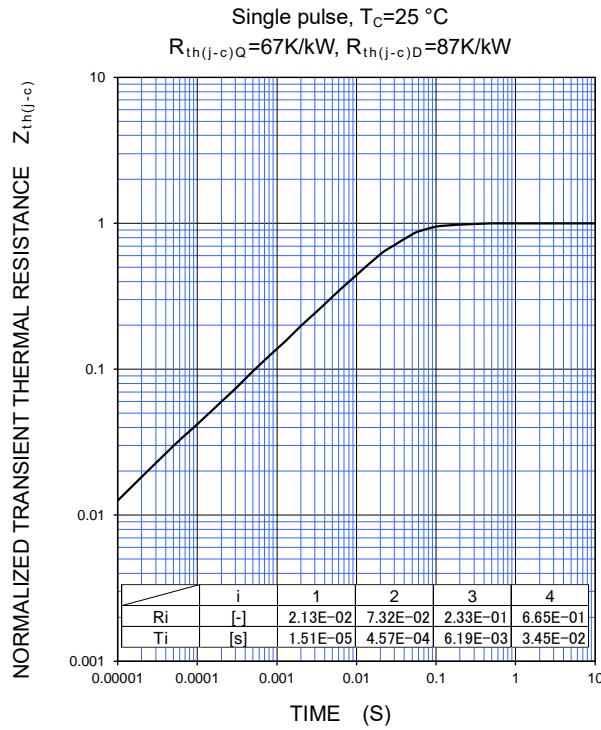
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{DD}=600\text{ V}$, $V_{GS}=\pm 15\text{ V}$, $I_D=600\text{ A}$, $T_{vj}=150\text{ }^\circ\text{C}$, $L_{s_ext}=12\text{nH}$
INDUCTIVE LOAD, PER PULSE

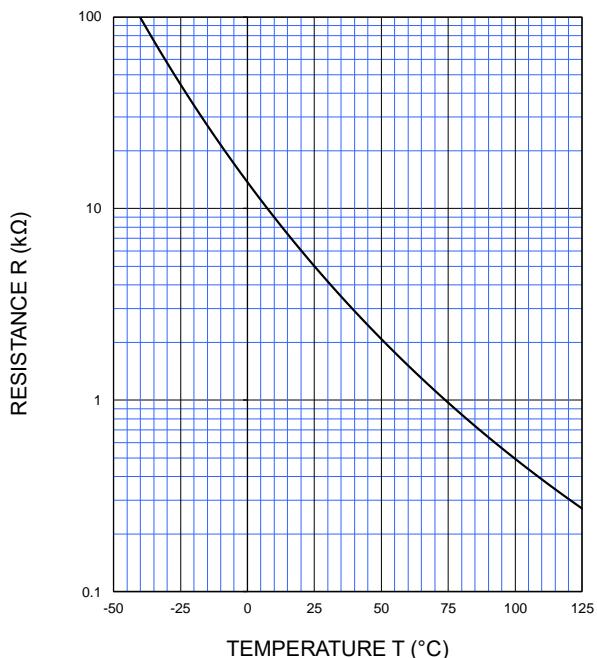
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{DD}=600\text{ V}$, $V_{GS}=\pm 15\text{ V}$, $I_D=600\text{ A}$, $T_{vj}=150\text{ }^\circ\text{C}$, $L_{s_ext}=12\text{nH}$
INDUCTIVE LOAD, PER PULSE



PERFORMANCE CURVESTRANSIENT THERMAL IMPEDANCE
CHARACTERISTICS
(MAXIMUM)

NTC thermistor part

TEMPERATURE
CHARACTERISTICS
(TYPICAL)

Note: The characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Important Notice

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